High Voltage NPN Silicon Power Transistors

This series is designed for line operated audio output amplifier, SWITCHMODE power supply drivers and other switching applications.

Features

- Popular TO-220 Plastic Package
- Complementary to the MJE5730 and MJE5731 Series
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	TIP47	TIP48	TIP50	Unit
Collector - Emitter Voltage	V _{CEO}	250	300	400	Vdc
Collector - Base Voltage	V _{CB}	350	400	500	Vdc
Emitter - Base Voltage	V _{EB}		5.0		Vdc
Collector Current – Continuous	I _C		1.0		Adc
Collector Current - Peak	I _{CM}		2.0		
Base Current	Ι _Β	0.6			Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32		W W/°C	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.0 0.016		W W/°C	
Unclamped Inducting Load Energy (See Figure 8)	E	20		mJ	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-6	65 to +15	50	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

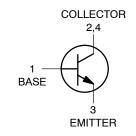
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

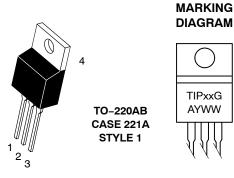


ON Semiconductor®

www.onsemi.com

1.0 AMPERE **POWER TRANSISTORS NPN SILICON** 250-300-400 VOLTS **40 WATTS**





TIPxx = Device Code = 47, 48, or 50 XX = Assembly Location = Year WW = Work Week = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•		•	•	•
Collector-Emitter Sustaining Voltage (Note 1) $(I_C = 30 \text{ mAdc}, I_B = 0)$	TIP47 TIP48 TIP50	V _{CEO(sus)}	250 300 400	- - -	Vdc
Collector Cutoff Current $(V_{CE} = 150 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 200 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 300 \text{ Vdc}, I_B = 0)$	TIP47 TIP48 TIP50	I _{CEO}	- - -	1.0 1.0 1.0	mAdc
Collector Cutoff Current	TIP47 TIP48 TIP50	I _{CES}	- - -	1.0 1.0 1.0	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		I _{EBO}	-	1.0	mAdc
ON CHARACTERISTICS (Note 1)	•		•	•	•
DC Current Gain $(I_C = 0.3 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 1.0 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$		h _{FE}	30 10	150	-
Collector–Emitter Saturation Voltage ($I_C = 1.0$ Adc, $I_B = 0.2$ Adc)		V _{CE(sat)}	-	1.0	Vdc
Base-Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 10 Vdc)		V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS					_
Current-Gain - Bandwidth Product (I _C = 0.1 Adc, V _{CE} = 10 Vdc, f = 2.0 MHz)		f _T	10	-	MHz
Small-Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	25	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse width $\leq 300 \ \mu s$, Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping
TIP47G	TO-220 (Pb-Free)	50 Units / Rail
TIP48G	TO-220 (Pb-Free)	50 Units / Rail
TIP49G	TO-220 (Pb-Free)	50 Units / Rail
TIP50G	TO-220 (Pb-Free)	50 Units / Rail

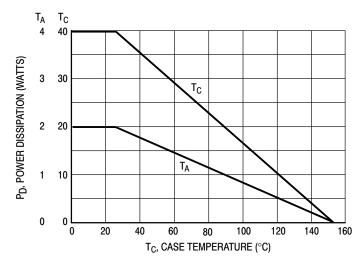


Figure 1. Power Derating

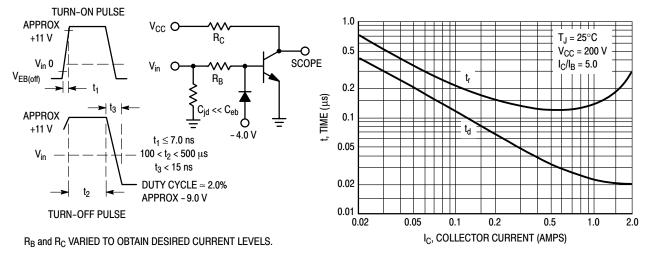


Figure 2. Switching Time Equivalent Circuit

Figure 3. Turn-On Time

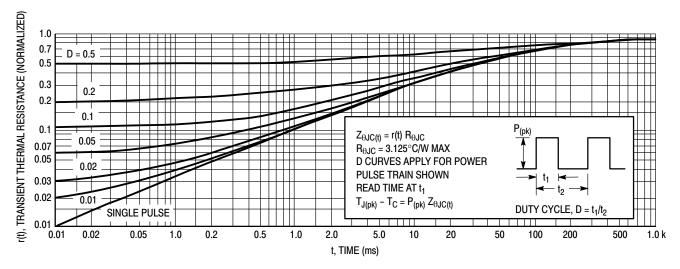


Figure 4. Thermal Response

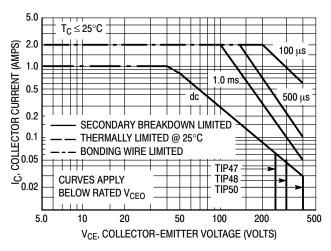


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

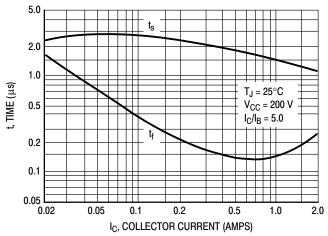


Figure 6. Turn-Off Time

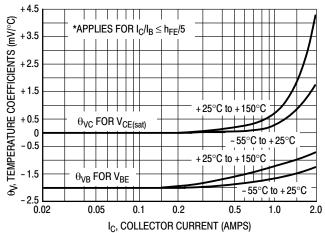
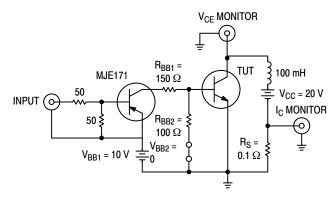


Figure 7. Temperature Coefficients



Note A: Input pulse width is increased until $I_{CM} = 0.63$ A.

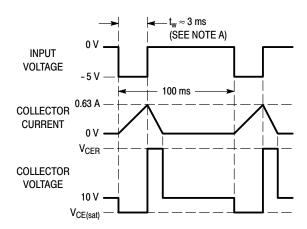


Figure 8. Inductive Load Switching

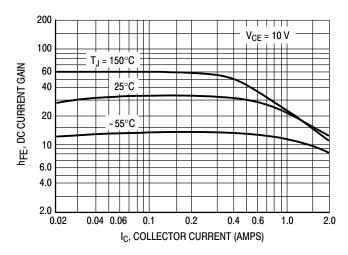


Figure 9. DC Current Gain

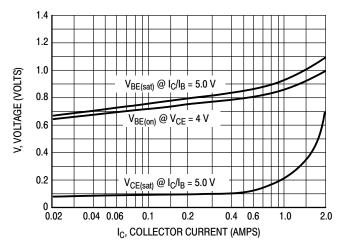
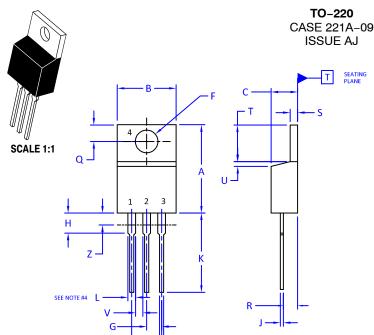


Figure 10. "On" Voltages

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





DATE 05 NOV 2019

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES

NOTES:

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELA
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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